










	<h2 style="color: red;">FQP7N80C</h2>
	Hersteller-Teilenummer: FQP7N80C
	Hersteller / Marke: AMI Semiconductor / ON Semiconductor
	Teil der Beschreibung: MOSFET N-CH 800V 6.6A TO-220
	Datenblätter: <ul style="list-style-type: none">  1.FQP7N80C.pdf  2.FQP7N80C.pdf
	RoHs Status: Bleifrei / RoHS-konform
	Lagerzustand: New original, 48671 pcs Stock Available.
	Liefern von: Hong Kong
	Versandweg: DHL/Fedex/TNT/UPS/EMS
<p>Image may be representation. See specs for product details.</p>	

Spezifikationen

Teilenummer	FQP7N80C
Hersteller	AMI Semiconductor / ON Semiconductor
Beschreibung	MOSFET N-CH 800V 6.6A TO-220
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs,
Teilstatus	48671 pcs Stock
Hersteller Standard Vorlaufzeit	6 Weeks
detaillierte Beschreibung	N-Channel 800V 6.6A (Tc) 167W (Tc) Through Hole
Serie	QFET®
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Through Hole
Verpackung / Gehäuse	TO-220-3
Supplier Device-Gehäuse	TO-220-3
Verlustleistung (max)	167W (Tc)
Typ FET	N-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	800V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	6.6A (Tc)
Rds On (Max) @ Id, Vgs	1.9 Ohm @ 3.3A, 10V
VGS (th) (Max) @ Id	5V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	35nC @ 10V
Eingabekapazität (Ciss) (Max) @ Vds	1680pF @ 25V
Antriebsspannung (Max Rds On, Min Rds On)	10V
Vgs (Max)	±30V
Verpackung	Tube
Bleifreier Status / RoHS-Status	Lead free / RoHS Compliant
Feuchtigkeitsempfindlichkeitsniveau (MSL)	1 (Unlimited)



















































FQP7N80C ist neu im Original, Suche FQP7N80C Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie FQP7N80C AMI Semiconductor / ON Semiconductor mit Garantie und Vertrauen. Anfrage FQP7N80C: Info@Y-IC.com

Sie können auch interessiert sein:

 <p>FQP7N80 Fairchild/ON Semiconductor MOSFET N-CH 800V 6.6A TO-220</p>	 <p>FQP7P20 AMI Semiconductor / ON Semiconductor MOSFET P-CH 200V 7.3A TO-220</p>	 <p>FQP7P06 Fairchild/ON Semiconductor MOSFET P-CH 60V 7A TO-220</p>	 <p>FQP80N06 F F TO220</p>
 <p>FQP7P06 AMI Semiconductor / ON Semiconductor MOSFET P-CH 60V 7A TO-220</p>	 <p>FQP7P20 Fairchild/ON Semiconductor MOSFET P-CH 200V 7.3A TO-220</p>	 <p>FQP7N80 AMI Semiconductor / ON Semiconductor MOSFET N-CH 800V 6.6A TO-220</p>	 <p>FQP7N65C AMI Semiconductor / ON Semiconductor MOSFET N-CH 650V 7A TO-220</p>

heiße Teile

Mehr

 FQP6N40C	 FQP6N40CF	 FQP6N40CF	 FQP6N50C	 FQP6N50C
 FQP6N60C	 FQP6N60C	 FQP6N80C	 FQP6N80C	 FQP6N90C
 FQP6N90C	 FQP70N03L	 FQP70N06	 FQP70N06C	 FQP70N08
 FQP70N08	 FQP70N10	 FQP70N10	 FQP7N10L	 FQP7N10L
 FQP7N20L	 FQP7N20L	 FQP7N60C	 FQP7N65C	 FQP7N65C
 FQP7N80C	 FQP85N06	 FQP85N06	 FQP8N50C	 FQP8N60C
 FQP8N60C	 FQP8N65C	 FQP8N80C	 FQP8N80C	 FQP8N90C
 FQP8N90C	 FQP90N08	 FQP90N08	 FQP90N10V2	 FQP90N10V2
 FQP9N08L	 FQP9N08L	 FQP9N25C	 FQP9N25C	 FQP9N50C
 FQP9N50C	 FQP9N65C	 FQP9N90C	 FQP9N90C	 FQPF10N20

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